

GNOA - GNOM

PRV : 50 - 1000 Volts
Io : 1.5 Amperes

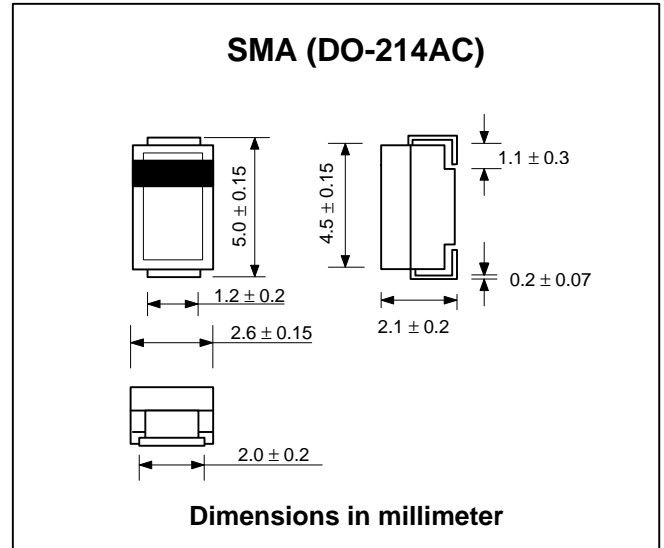
FEATURES :

- * Glass passivated chip
- * High current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : SMA Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Lead Formed for Surface Mount
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.067 gram

GLASS PASSIVATED JUNCTION SILICON SURFACE MOUNT



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	GNOA	GNOB	GNOB	GNOE	GNOG	GNOH	GNOJ	GNOK	GNOM	UNIT
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	500	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	350	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	500	600	800	1000	V
Maximum Average Forward Current $T_a = 75^\circ\text{C}$	$I_{F(AV)}$	1.5									A
Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on rated load (JEDEC Method)	I_{FSM}	50									A
Maximum Forward Voltage at $I_F = 1.5$ Amps.	V_F	1.1									V
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at rated DC Blocking Voltage $T_a = 100^\circ\text{C}$	I_R	5.0									μA
	$I_{R(H)}$	50									μA
Typical Junction Capacitance (Note1)	C_J	30									pF
Junction Temperature Range	T_J	- 65 to + 150									$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 65 to + 150									$^\circ\text{C}$

Note :

(1) Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc

RATING AND CHARACTERISTIC CURVES (GNOA - GNOM)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

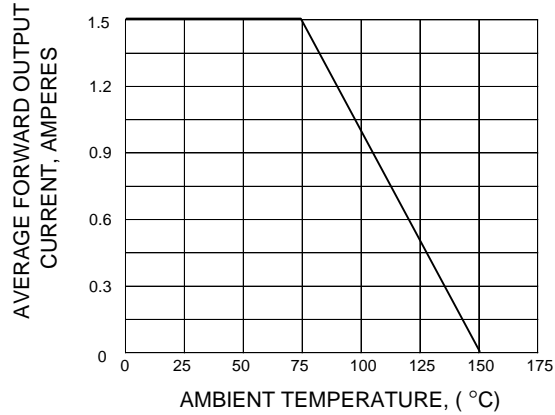


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

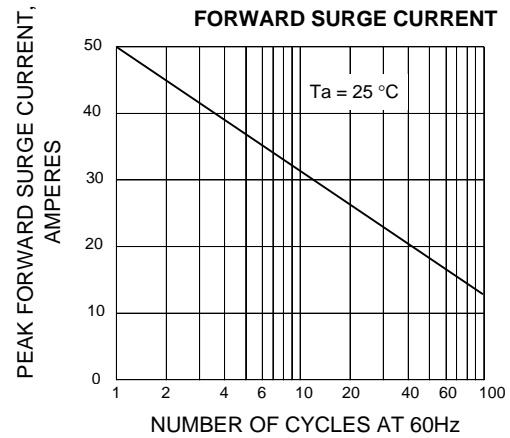


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

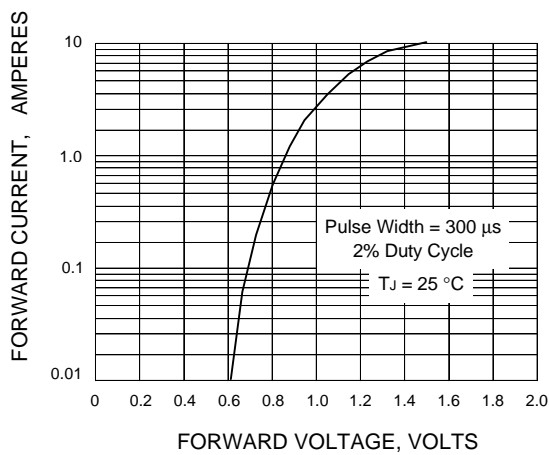


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

